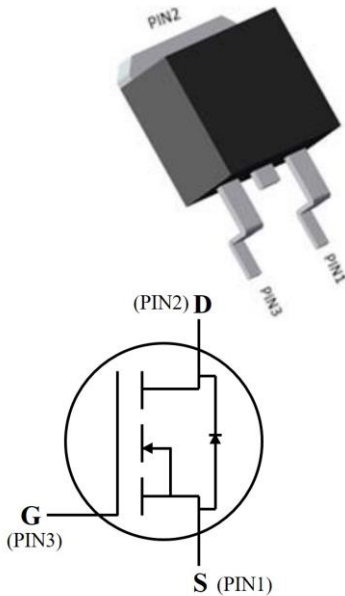


## Silicon Carbide Power MOSFET (N-Channel Enhancement)

$V_{DS}$	1200V
$I_D$ (25°C)	13.5A
$R_{DS(on)}$	240mΩ



### Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Maximum working temperature at 175 °C
- High blocking voltage
- Fast Intrinsic diode with low recovery current
- High-frequency operation
- Halogen free, RoHS compliant
- AEC-Q101 qualified

### Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

### Mechanical Data

- **Package:** TO-263
- **Terminals:** Tin plated leads
- **Polarity:** As marked

### ■Maximum Ratings ( $T_C=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE	TEST CONDITIONS	NOTE
Device marking code				D2120240BGH	
Drain source voltage @ $T_j=25^\circ\text{C}$	$V_{DS,max}$	V	1200	$V_{GS}=0\text{ V}$ , $I_D=100\mu\text{A}$	
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,max}$	V	-10/+25	Absolute maximum values (AC f > 1Hz, duty cycle < 1%)	Note1
Gate source voltage @ $T_j=25^\circ\text{C}$	$V_{GS,op}$	V	-5/+20	Recommended operational values	
Continuous drain current @ $T_c=25^\circ\text{C}$	$I_D$	A	13.5	$V_{GS}=20\text{V}$ , $T_c=25^\circ\text{C}$	Fig.14
Continuous drain current @ $T_c=110^\circ\text{C}$			9.5	$V_{GS}=20\text{V}$ , $T_c=110^\circ\text{C}$	
Pulse Drain Current	$I_{D,pulse}$	A	23	Limited by $t_{pw}$	Fig.15
Avalanche energy, Single Pulse	$E_{AS}$	mJ	312	$V_{DD}=100\text{V}$ , $I_D=5\text{A}$	
Power Dissipation	$P_{TOT}$	W	105	$T_c=25^\circ\text{C}$ , $T_j=175^\circ\text{C}$	Fig.13
Operating junction and Storage temperature range	$T_j, T_{stg}$	°C	-55 to +175		
Soldering temperature	$T_L$	°C	260	1.6mm (0.063") from case for 10s	
Mounting torque	$T_M$	Nm	0.6	M3 screw Maximum of mounting process: 3	



### ■Static Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Gate threshold voltage	V <sub>GS(th)</sub>	V		2.6		V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =5mA	Fig.4, 11
Drain source breakdown voltage	V <sub>(BR)DSS</sub>	V	1200			V <sub>GS</sub> =0, I <sub>D</sub> =100uA	
Zero gate voltage drain current	I <sub>DSS</sub>	uA		<1	50	V <sub>DS</sub> =1200V, V <sub>GS</sub> =0V	
				10	500	V <sub>DS</sub> =1200V, V <sub>GS</sub> =0V, T <sub>J</sub> =175°C	
Gate source leakage current	I <sub>GSS</sub>	nA			250	V <sub>GS</sub> =20V, V <sub>DS</sub> =0V	
Current drain source on-state resistance	R <sub>DS(on)</sub>	mΩ		240	320	V <sub>GS</sub> =20V, I <sub>D</sub> =5A	Fig.3, 5, 6
				400		V <sub>GS</sub> =20V, I <sub>D</sub> =5A, T <sub>J</sub> =175°C	
Transconductance	g <sub>f</sub>	S		4.3		V <sub>DS</sub> =12V, I <sub>D</sub> =15A	

### ■Dynamic Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Input capacitance	C <sub>iss</sub>	pF		559		V <sub>DS</sub> =800V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C, f=1MHz, V <sub>AC</sub> =25mV	Fig.10
Output capacitance	C <sub>oss</sub>			36			
Reverse capacitance	C <sub>rss</sub>			7.5			
Coss stored energy	E <sub>oss</sub>	uJ		14			Fig.12
Gate source charge	Q <sub>gs</sub>	nC		10		V <sub>DS</sub> =800V, V <sub>GS</sub> =5/20V, I <sub>D</sub> =5A	Fig.16
Gate drain charge	Q <sub>gd</sub>			25			
Gate charge	Q <sub>g</sub>			47			
Internal Gate Resistance	R <sub>G(int)</sub>	Ω		3.7		f=1MHz, V <sub>AC</sub> =25mV	

### ■Switching Characteristics (T<sub>c</sub>=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Turn on delay time	t <sub>d(on)</sub>	ns		23		V <sub>DD</sub> =800V, V <sub>GS</sub> =0/+20V, I <sub>D</sub> =4A, R <sub>L</sub> =200Ω, R <sub>G(ext)</sub> =10Ω	
Rise time	t <sub>r</sub>			19			
Turn off delay time	t <sub>d(off)</sub>			40			
Fall time	t <sub>f</sub>			64			
Turn on switching energy	E <sub>on</sub>	uJ		10		V <sub>DD</sub> =800V, V <sub>GS</sub> =0/+20V, I <sub>D</sub> =5A, R <sub>G(ext)</sub> =2.7Ω	Fig.17, 18
Turn off switching energy	E <sub>off</sub>			10			



■Body diode characteristics (Tc=25°C unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Min.	Typ.	Max.	Test Conditions	Note
Diode forward voltage	V <sub>SD</sub>	V		3.1		V <sub>GS</sub> =0V, I <sub>SD</sub> =1.25A	Fig.8
Continuous diode forward current	I <sub>s</sub>	A		15.5		V <sub>GS</sub> =0V, Tc=25°C	
Reverse recovery time	t <sub>rr</sub>	nS		47		V <sub>DS</sub> =400V, V <sub>GS</sub> =0V, I <sub>SD</sub> =5A, di/dt=300A/uS	
Reverse recovery charge	Q <sub>rr</sub>	nC		36			
Peak reverse recovery current	I <sub>rrm</sub>	A		1.5			

Note 1: When using SiC Body Diode the maximum recommended V<sub>GS</sub> = -5V

■Thermal Characteristics (T<sub>a</sub>=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R <sub>θJ-C</sub>	°C/W	1.42

■Typical Characteristics

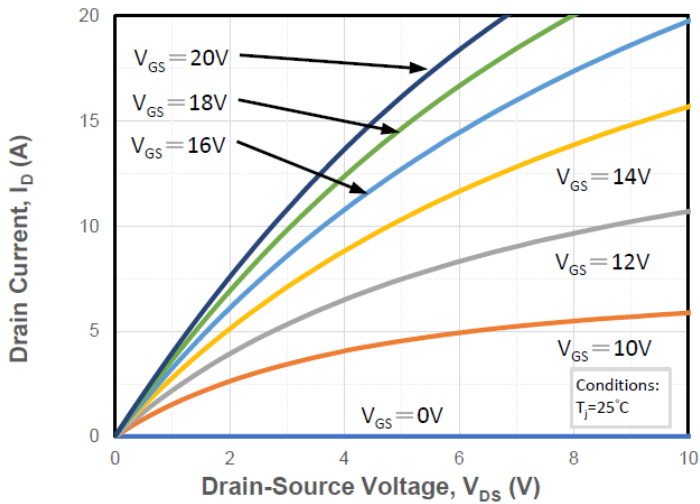


Figure 1. Output Characteristics T<sub>j</sub> = 25°C

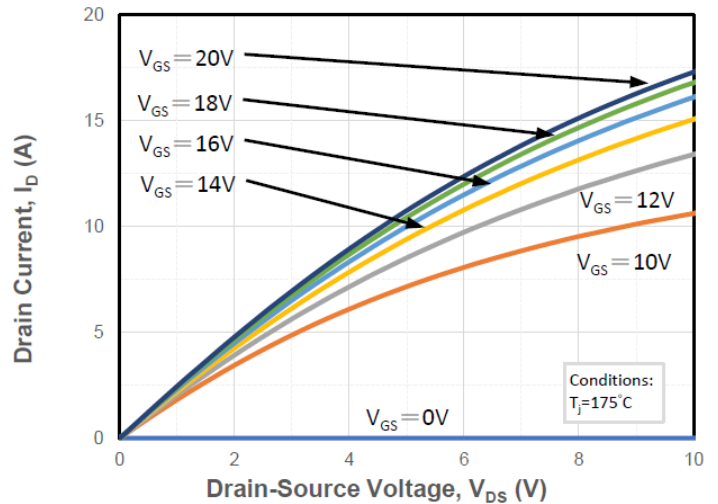


Figure2. Output Characteristics T<sub>j</sub> = 175°C

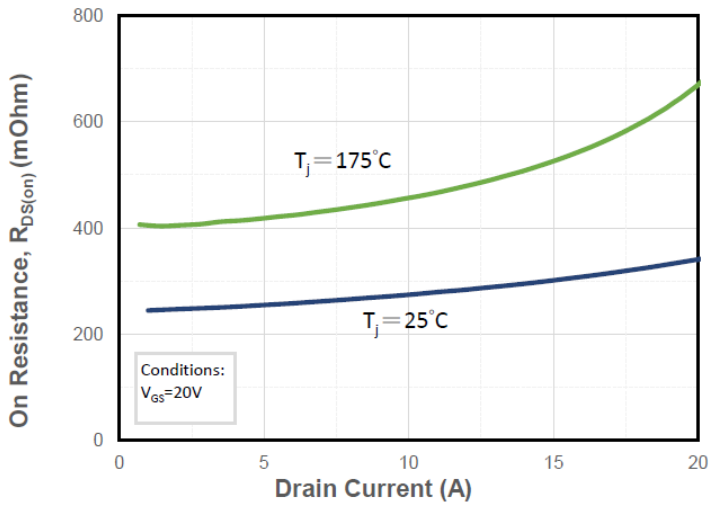


Figure 3. On-resistance vs. drain current

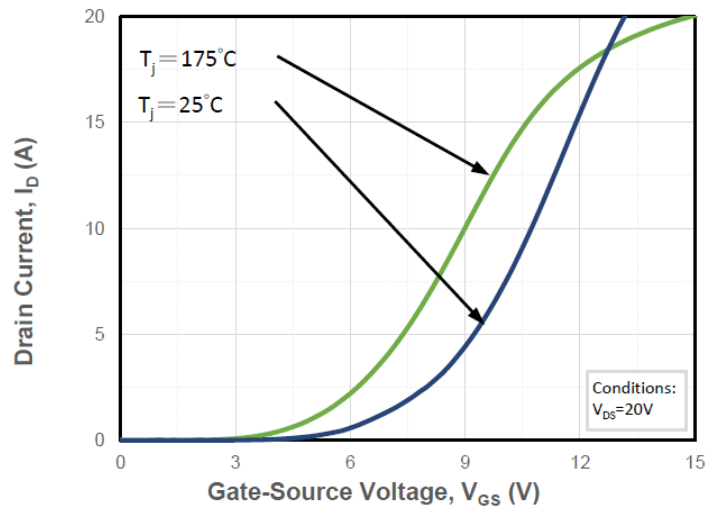


Figure 4. Transfer Characteristics for various Tj

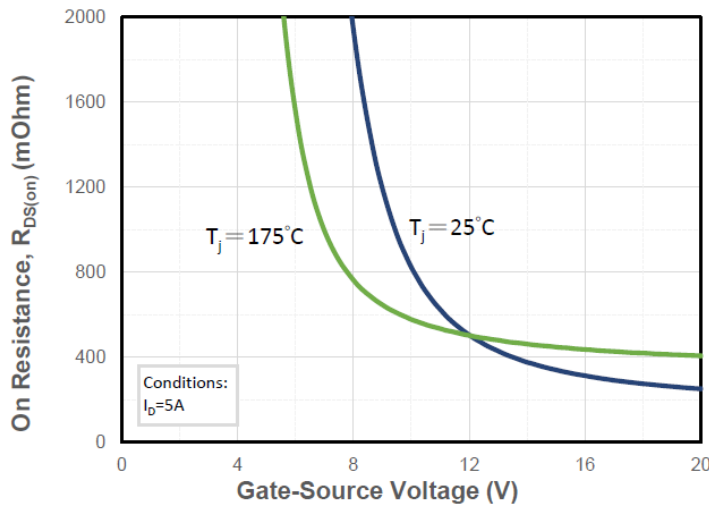


Figure 5. On-resistance vs. gate voltage for various Tj

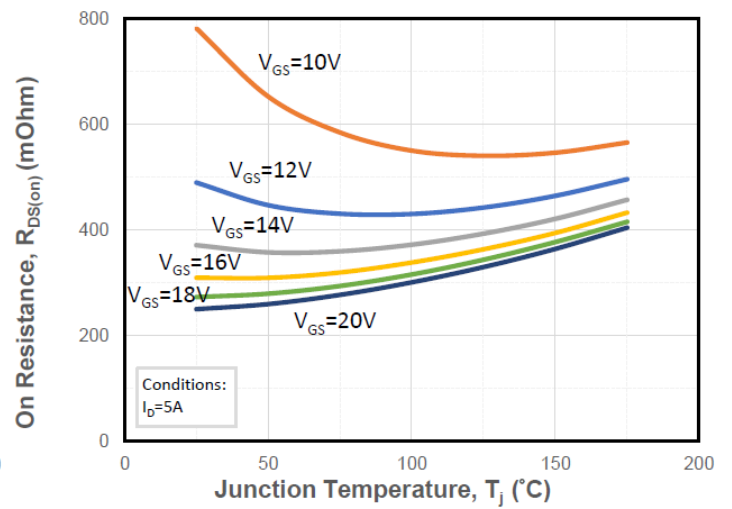


Figure 6. On-resistance vs. Temperature for various Gate voltage

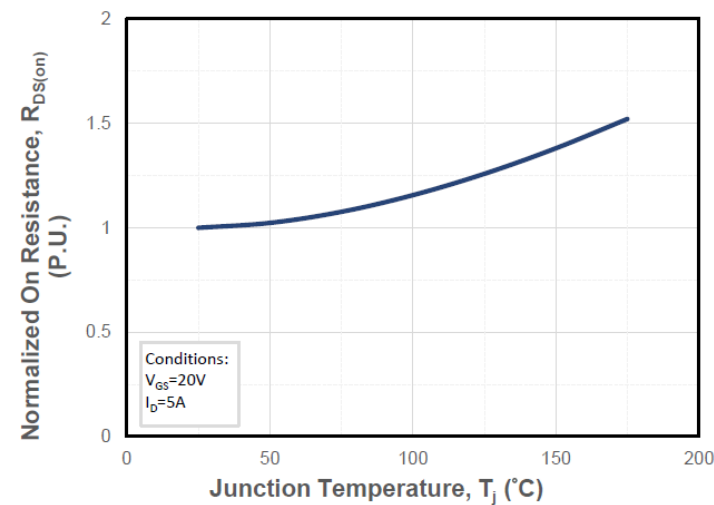


Figure 7. Normalized On-Resistance vs. Temperature

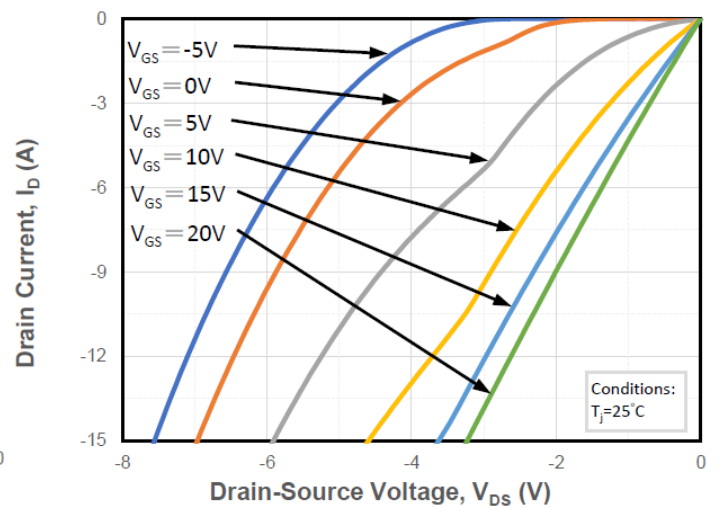


Figure 8. Reverse Output Characteristics at Tj = 25°C

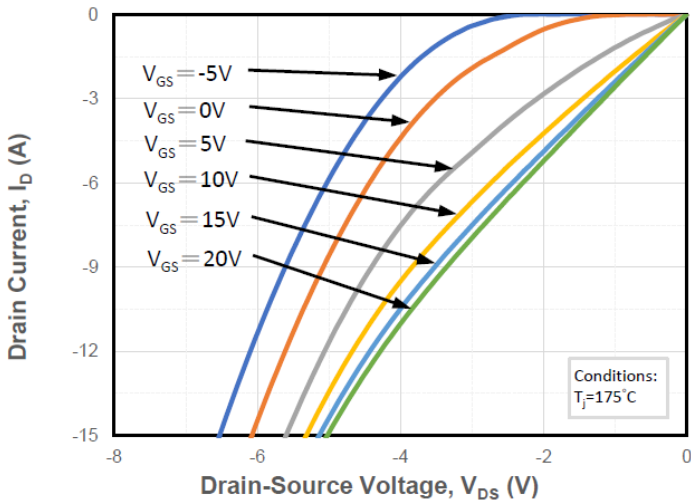


Figure 9. Reverse Output Characteristics at Tj = 175°C

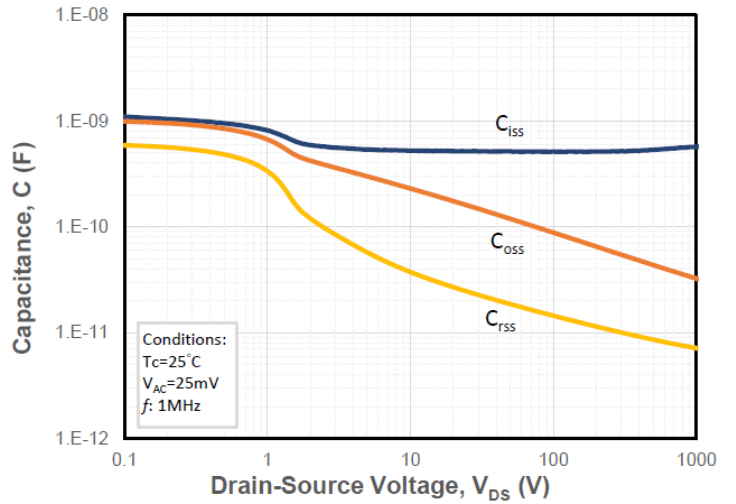


Figure 10. Capacitances vs. Drain to Source Voltage

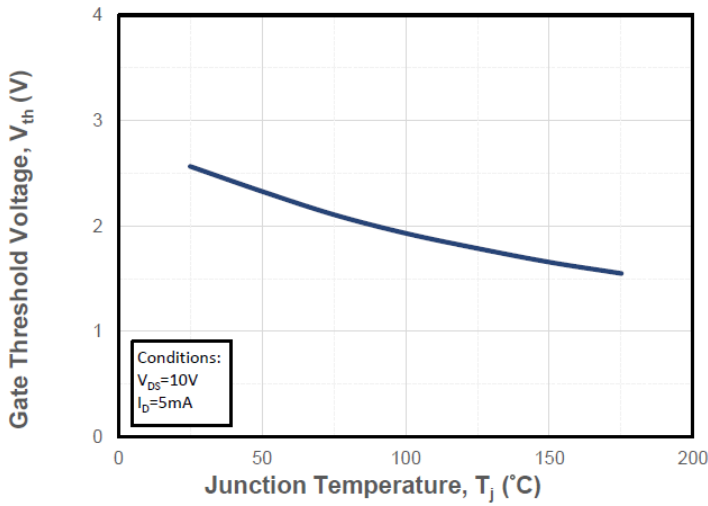


Figure 11. Threshold voltage vs. temperature

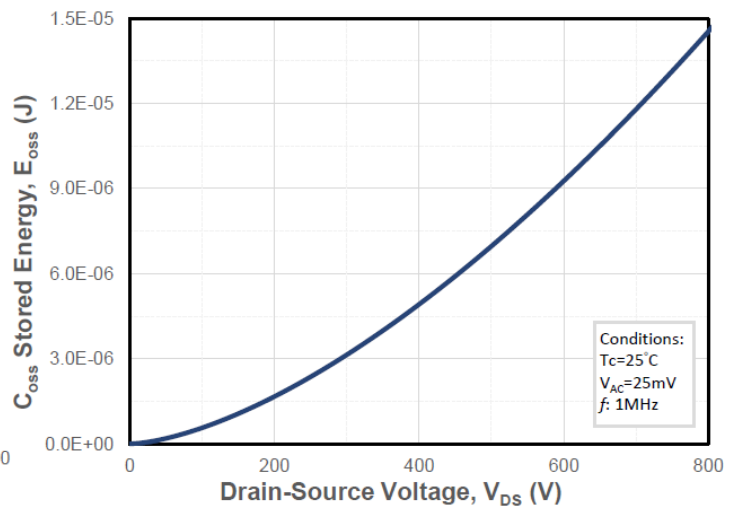


Figure 12. Output Capacitor Stored Energy

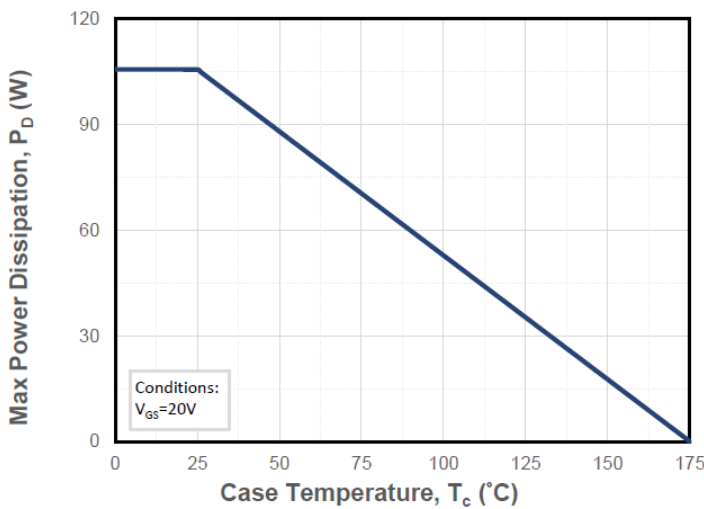


Figure 13. Maximum Power Dissipation Derating vs. Case Temperature

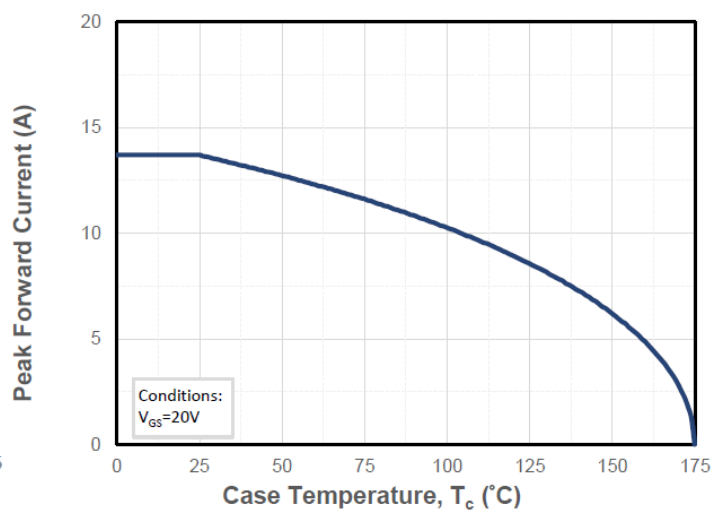


Figure 14. Drain Current Derating vs. Case Temperature

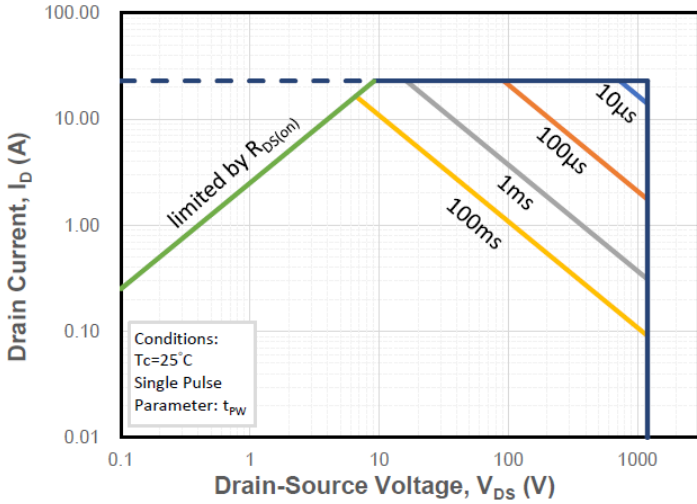


Figure 15. Safe Operating Area

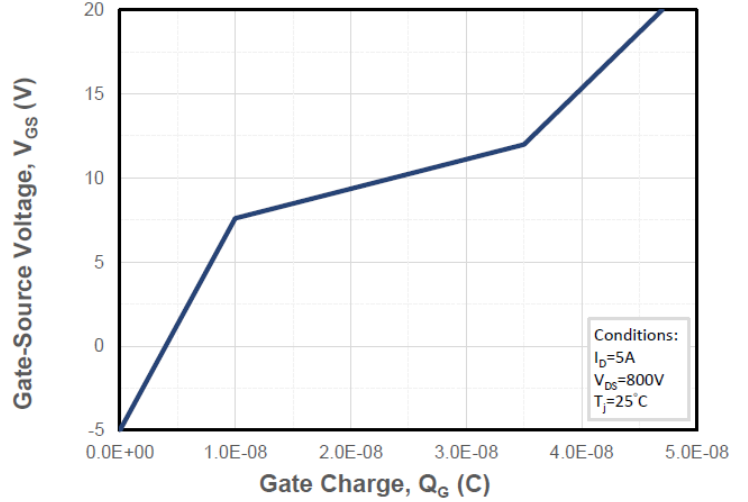


Figure 16. Gate Charge Characteristics

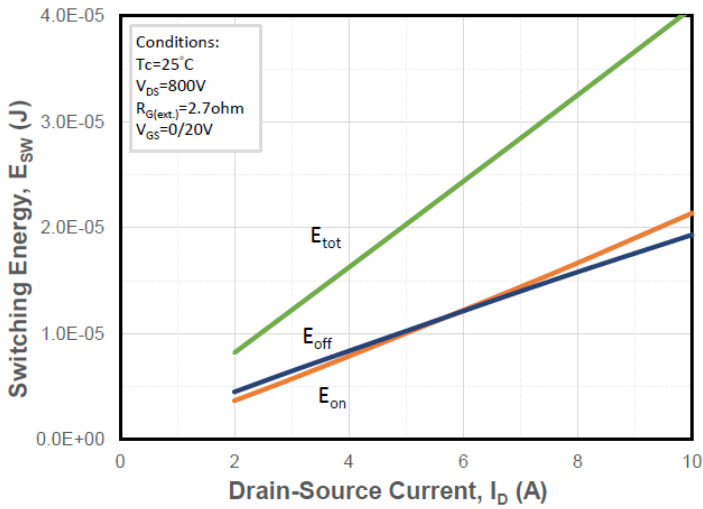


Figure 17. Clamped Inductive Switching Energy vs. Drain Current

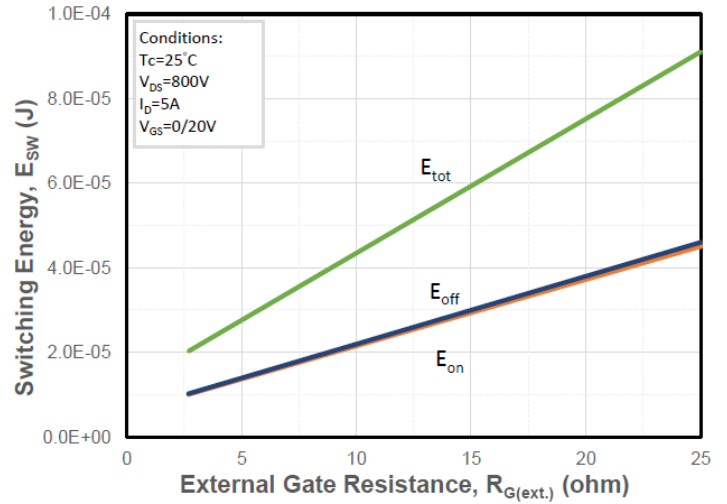


Figure 18. Clamped Inductive Switching Energy vs. External Gate Resistor ( $R_{G(ext.)}$ )

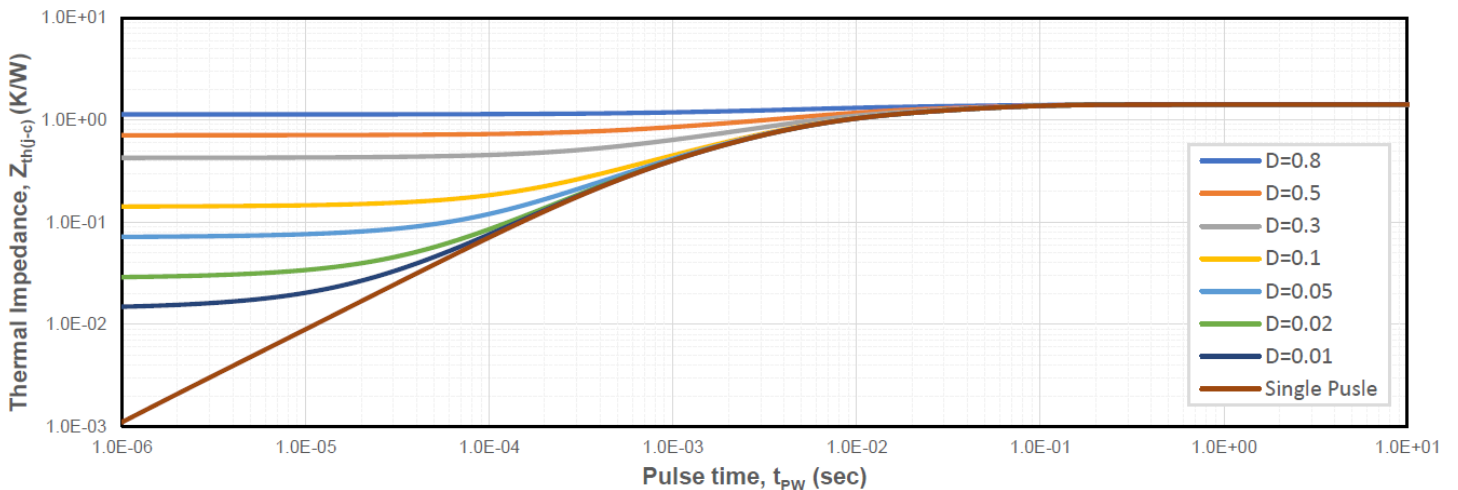


Figure 19. Transient Junction to Case Thermal Impedance

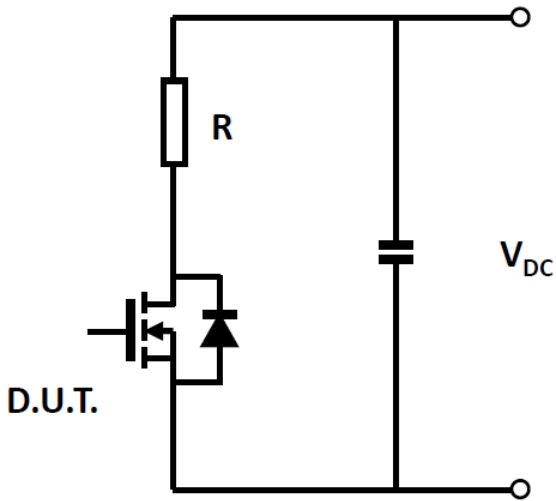


Figure 20. Schematic of Resistive Switching

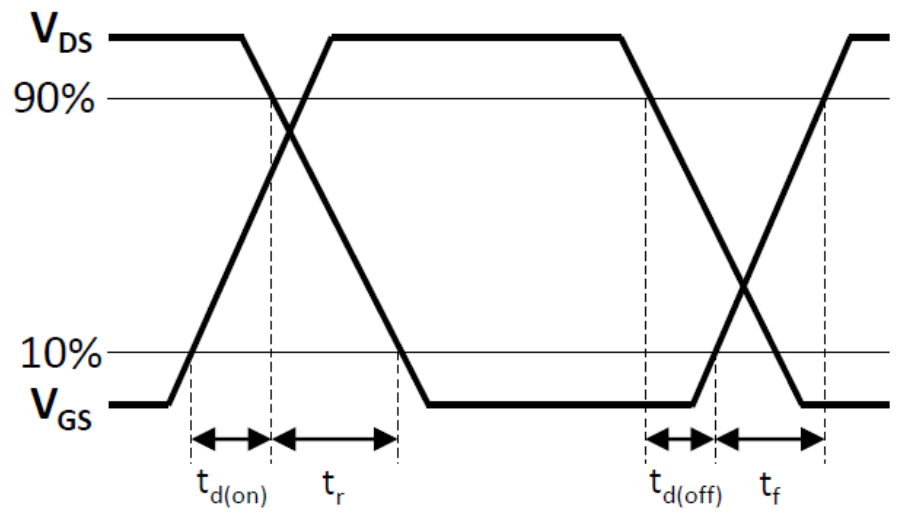
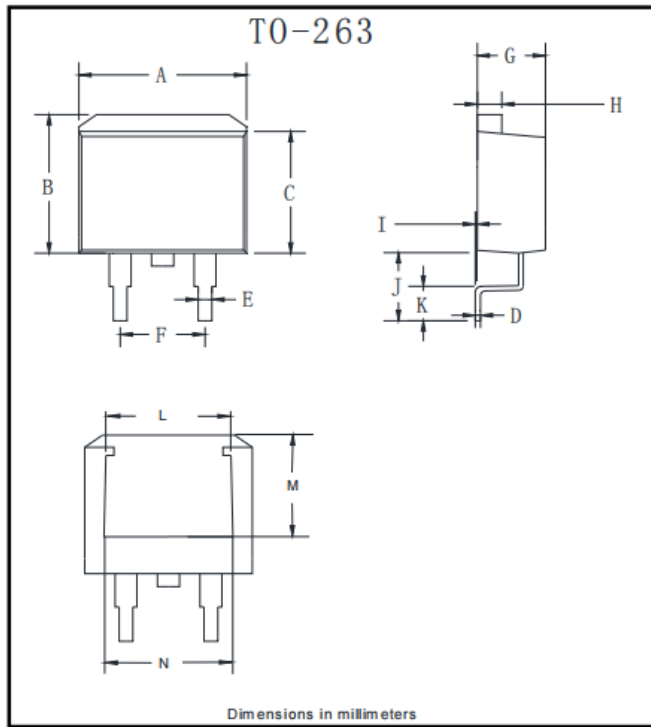


Figure 21. Switching Times Definition

## ■Outline Dimensions



<b>TO-263</b>		
Dim	Min	Max
A	9.5	11.5
B	9.7	10.5
C	8.4	9.0
D	0.28	0.64
E	0.68	0.94
F	4.55	5.6
G	4.04	5.10
H	1.14	1.4
I	0	0.2
J	4.9	6.05
K	1.79	2.79
L	7.3	7.9
M	6.2	6.8
N	7.6	8.2





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